
HSU88

Silicon Schottky Barrier Diode for Various Detector, Mixer

HITACHI

ADE-208-077F(Z)

Rev 6

June 1996

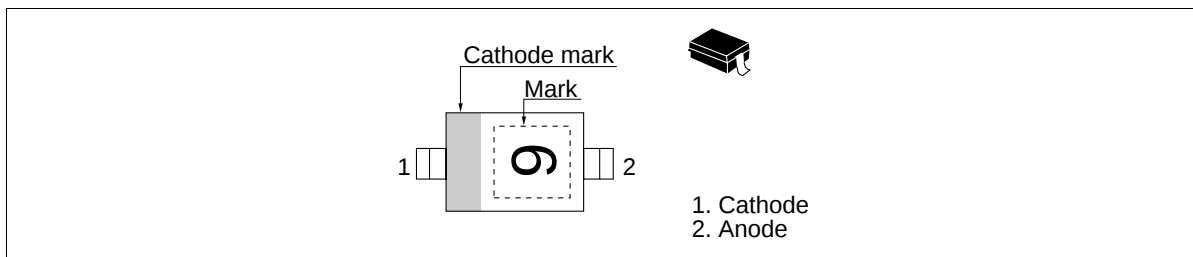
Features

- Low capacitance. (C=2.0pF max)
- Low forward voltage.
- Ultra small Resin Package (URP) is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSU88	9	URP

Outline



HSU88

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	VR	10	V
Average rectified current	IO	15	mA
Junction temperature	TJ	125	°C
Storage temperature	Tstg	-55~+125	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	VF1	350	~	420	mV	IF = 1 mA
	VF2	500	~	580		IF = 10 mA
Reverse current	IR1	~	~	0.2	μA	VR = 2V
	IR2	~	~	10		VR = 10V
Capacitance	C	~	~	0.8	pF	VR = 0V, f = 1 MHz
ESD-Capability*1	~	30	~	~	V	C=200pF , Both forward and reverse direction 1 pulse.

Notes 1. Failure criterion ; IR ≥ 400nA at VR =2 V

Main Characteristic

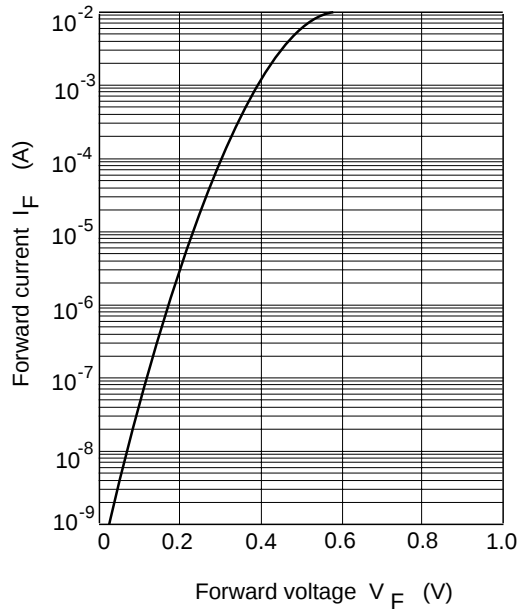


Fig.1 Forward current Vs. Forward voltage

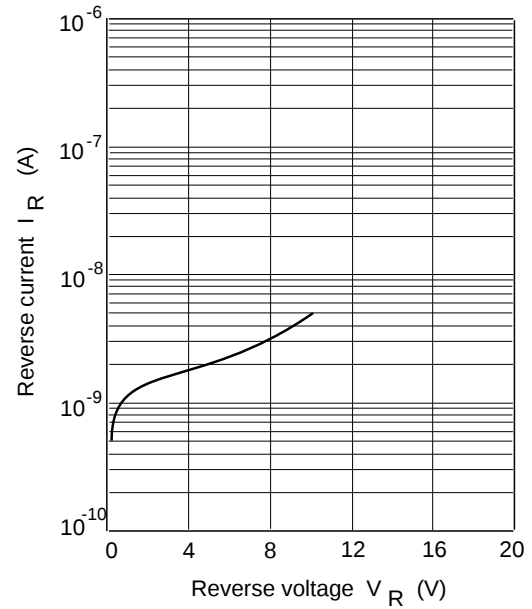


Fig.2 Reverse current Vs. Reverse voltage

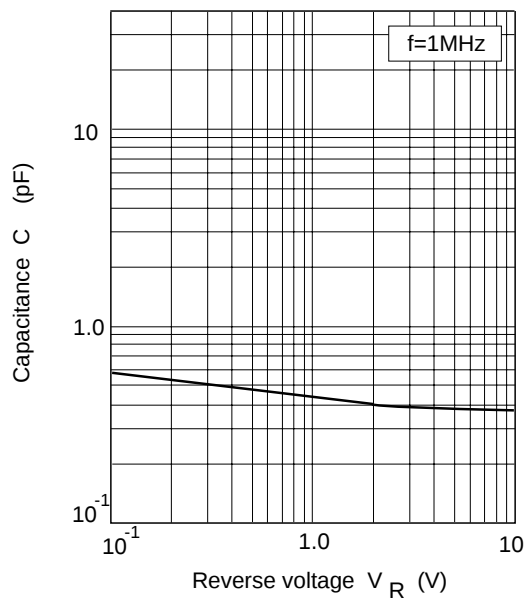


Fig.3 Capacitance Vs. Reverse voltage

HSU88

Package Dimensions

Unit : mm

